

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
30V	1.35mΩ @ V _{GS} = 10V	150A
	2.4mΩ @ V _{GS} = 4.5V	100A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low R_{DS(ON)} – Minimizes On-State Losses
- Excellent Q_{gd} x R_{DS(ON)} Product (FOM)
- Advanced Technology for DC-DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- 100% Unclamped Inductive Switching – Ensures More Reliability
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: PowerDI5060-8 (Type K)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.097 grams (Approximate)

PowerDI5060-8 (Type K)

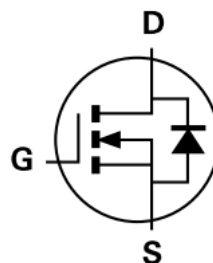


Top View

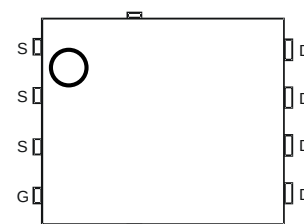


Pin1

Bottom View



Internal Schematic



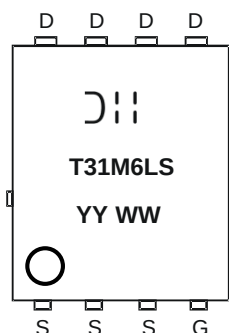
Top View
Pin Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT31M6LPS-13	PowerDI5060-8 (Type K)	2,500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



DMT31M6LS = Manufacturer's Marking
T31M6LS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 16 = 2016)
WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 6)	I _D	35.8 28.6	A
Continuous Drain Current, V _{GS} = 10V (Note 7)	I _D	150 128	A
Maximum Continuous Body Diode Forward Current (Note 7)	I _S	83	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I _{DM}	160	A
Avalanche Current, L=1mH	I _{AS}	25.5	A
Avalanche Energy, L=1mH	E _{AS}	325	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	1.3	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	99	°C/W
Total Power Dissipation (Note 6)	P _D	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	50	°C/W
Total Power Dissipation (Note 7)	P _D	100	W
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	1.2	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = 20V, V _{DS} = 0V V _{GS} = -16V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.1	1.35	mΩ	V _{GS} = 10V, I _D = 20A
		—	1.6	2.4		V _{GS} = 4.5V, I _D = 20A
Diode Forward Voltage	V _{SD}	—	—	1.2	V	V _{GS} = 0V, I _S = 2A
DYNAMIC CHARACTERISTICS (Note 19)						
Input Capacitance	C _{iss}	—	7019	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	3372	—		
Reverse Transfer Capacitance	C _{rss}	—	554	—		
Gate Resistance	R _g	—	0.94	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	123	—	nC	V _{DD} = 15V, I _D = 20A
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	59.1	—		
Gate-Source Charge	Q _{gs}	—	14.9	—		
Gate-Drain Charge	Q _{gd}	—	24.5	—		
Turn-On Delay Time	t _{D(ON)}	—	8.6	—	ns	V _{DD} = 15V, V _{GS} = 10V, R _g = 3Ω, I _D = 20A
Turn-On Rise Time	t _r	—	20.2	—		
Turn-Off Delay Time	t _{D(OFF)}	—	71.5	—		
Turn-Off Fall Time	t _f	—	42.3	—		
Body Diode Reverse Recovery Time	t _{RR}	—	37.2	—	ns	I _F = 20A, dI/dt = 500A/μs
Body Diode Reverse Recovery Charge	Q _{RR}	—	73.6	—	nC	

- Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. Thermal resistance from junction to soldering point (on the exposed drain pad).
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

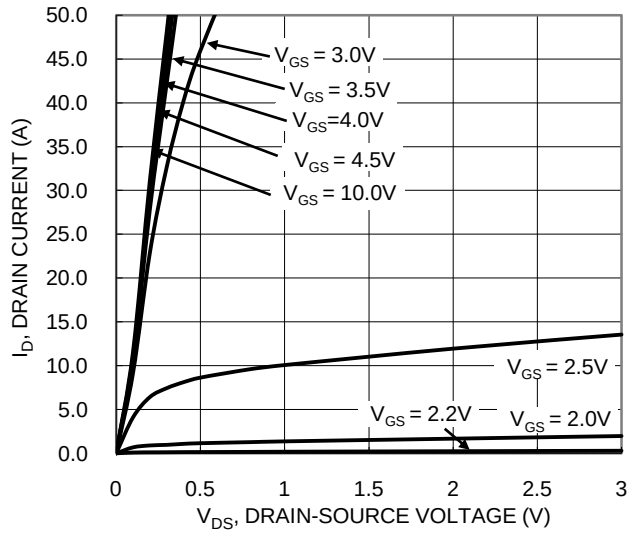


Figure 1. Typical Output Characteristic

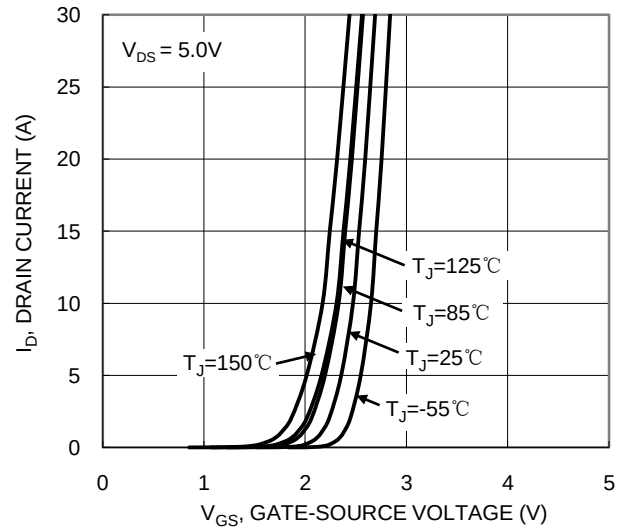


Figure 2. Typical Transfer Characteristic

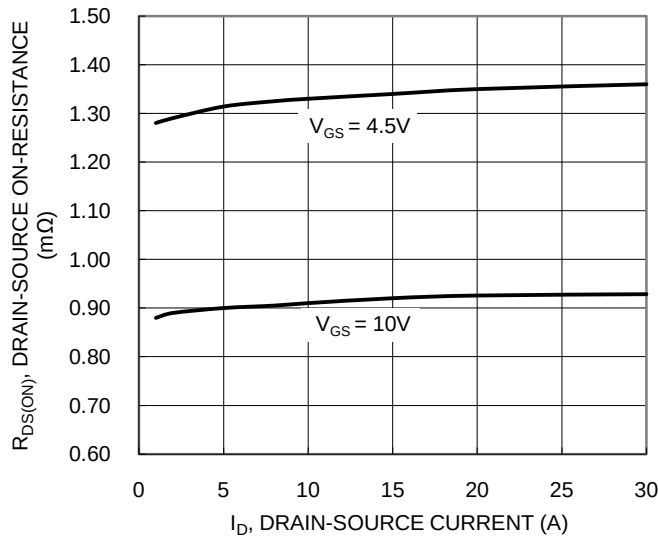


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

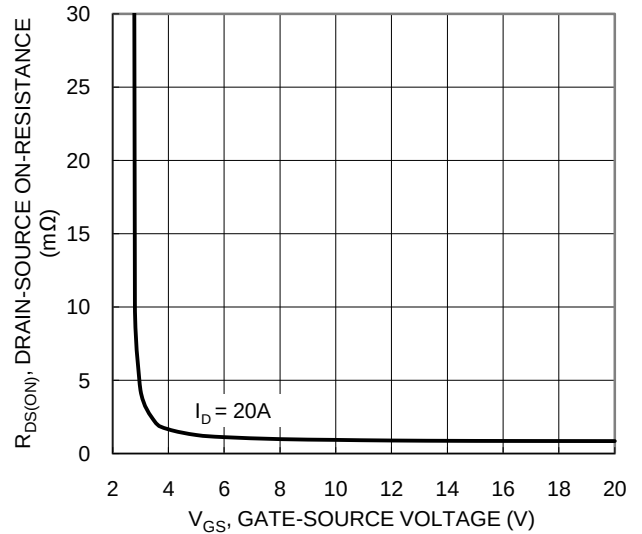


Figure 4. Typical Transfer Characteristic

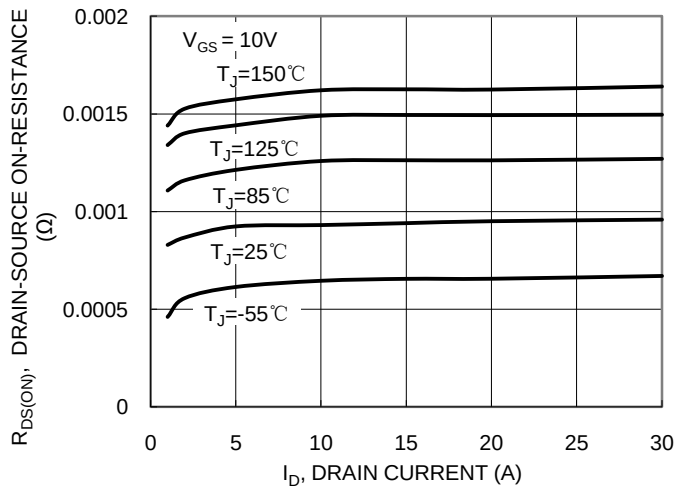


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

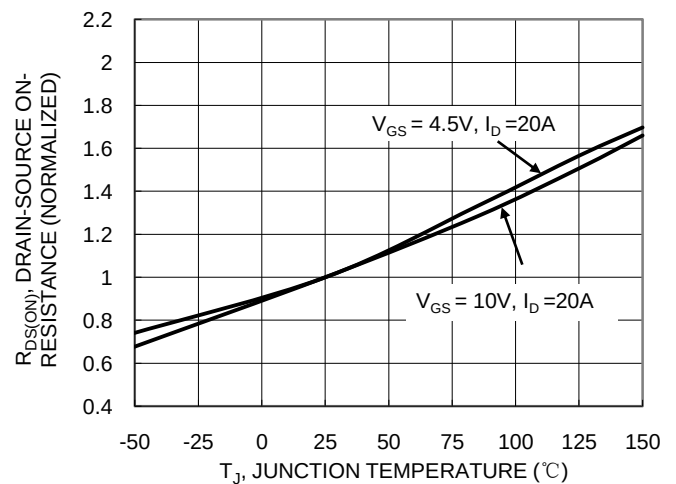
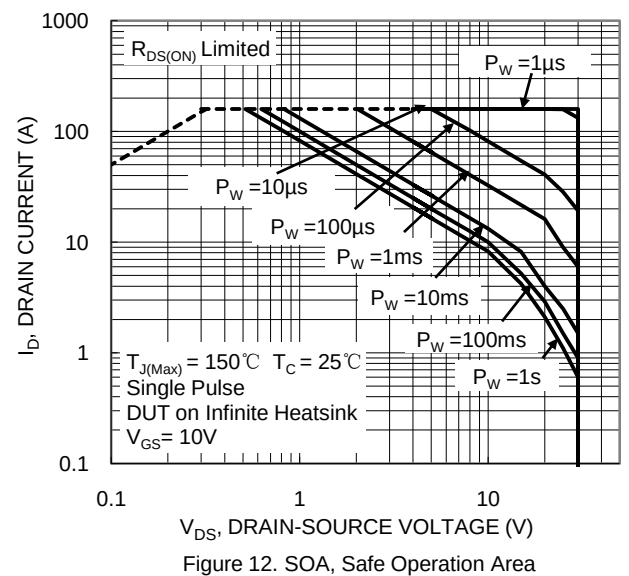
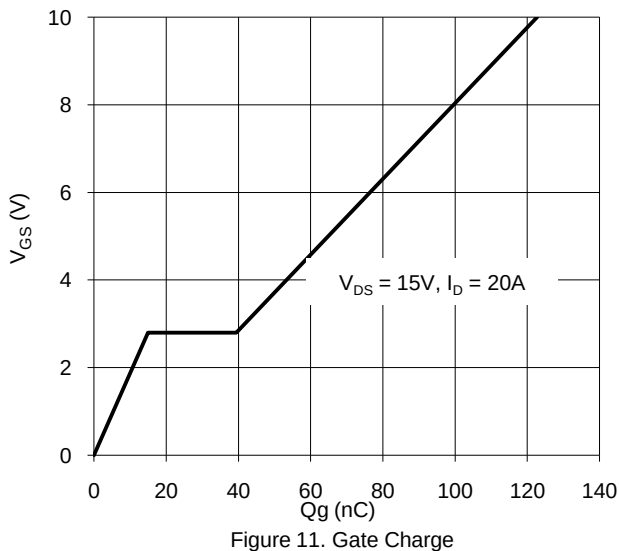
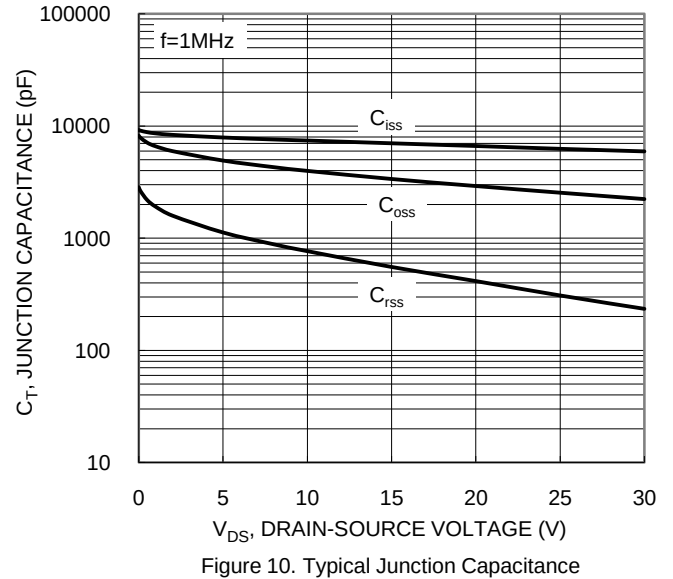
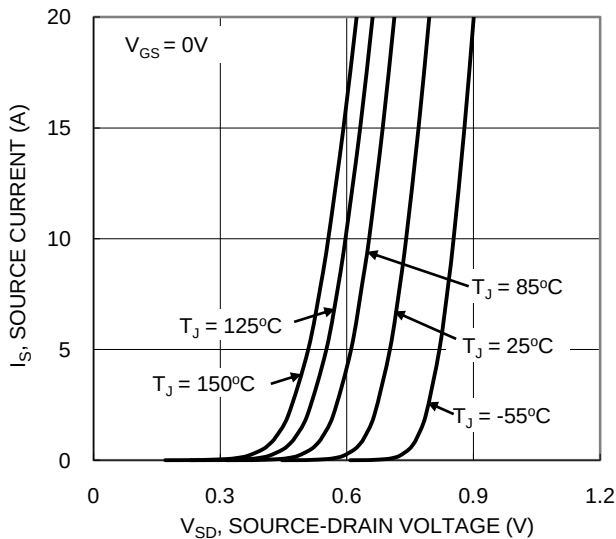
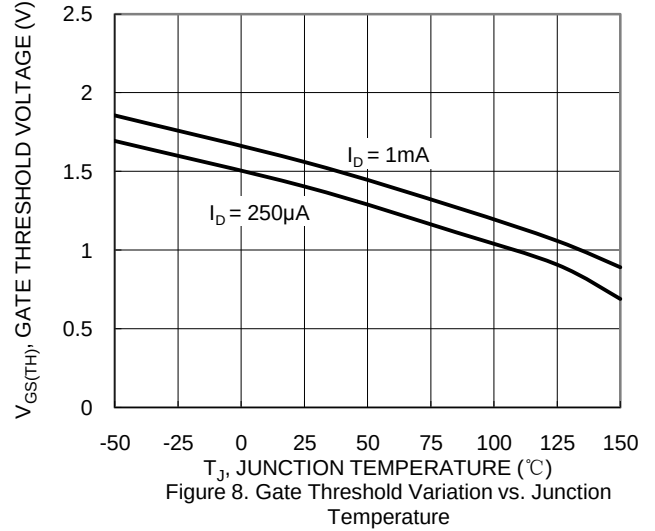
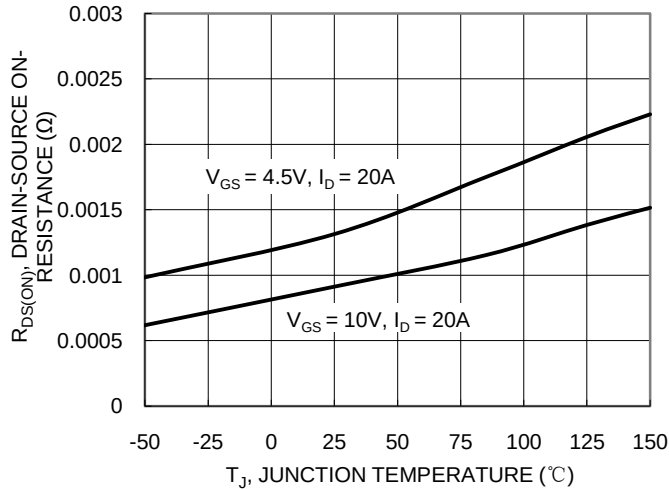


Figure 6. On-Resistance Variation with Temperature



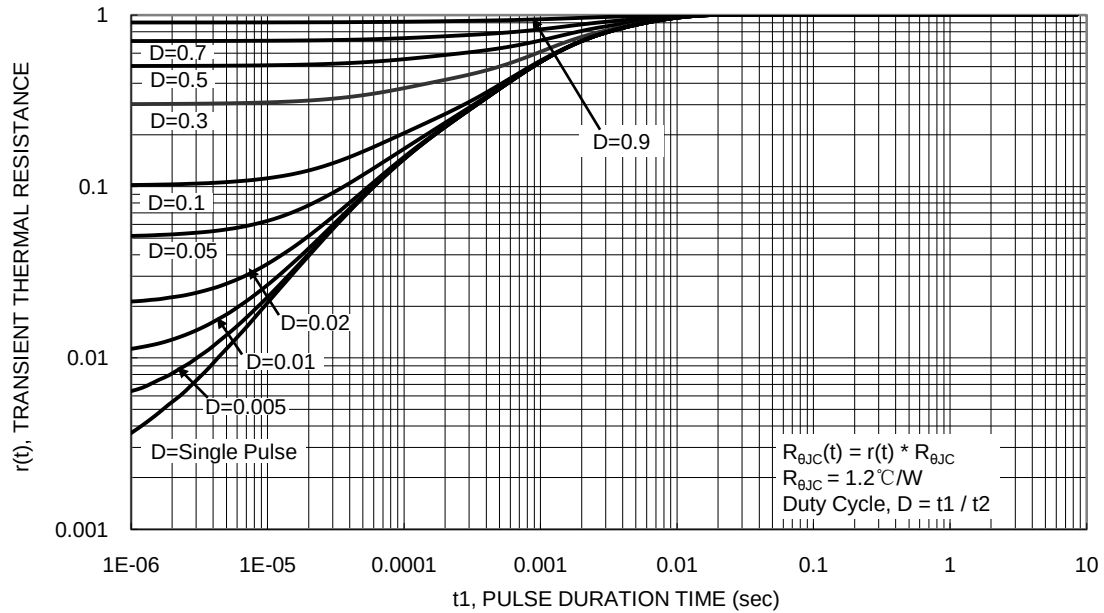
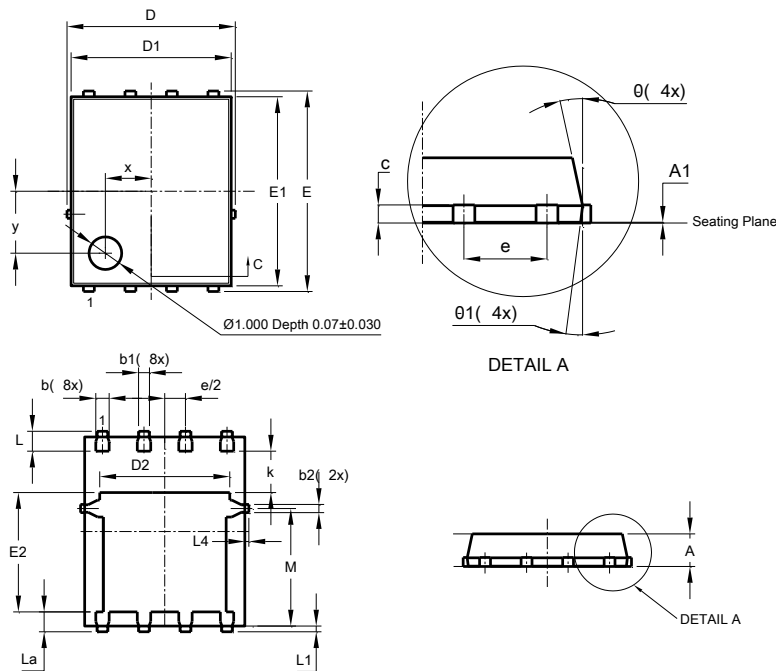


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (Type K)

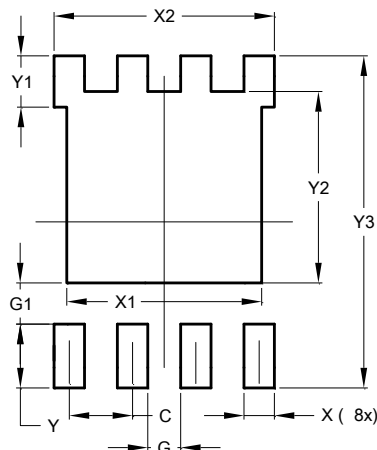


PowerDI5060-8 (Type K)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	0.02
b	0.33	0.51	0.41
b1	0.300	0.366	0.333
b2	0.20	0.35	0.25
c	0.23	0.33	0.277
D	5.15 BSC		
D1	4.85	4.95	4.90
D2	-	-	3.98
E	6.15 BSC		
E1	5.75	5.85	5.80
E2	3.56	3.725	3.66
E	1.27BSC		
k	-	-	1.27
L	0.51	0.71	0.61
La	0.51	0.675	0.61
L1	0.05	0.20	0.175
L4	-	-	0.125
M	3.50	3.71	3.605
x	-	-	1.400
y	-	-	1.900
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (Type K)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	3.910
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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